Renesas Electronics America Inc - M30622F8PFP#U3C Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	85
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-BQFP
Supplier Device Package	100-QFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30622f8pfp-u3c

Table 1.9 Product Code of Flash Memory version for M16C/62PT

		Product Code	Package	Internal ROM (User ROM Area Without Block A, Block 1)		Internal ROM (Block A, Block 1)		Operating Ambient Temperature
				Program and Erase Endurance	Temperature Range	Program and Erase Endurance	Temperature Range	
Flash memory Version	T Version	B	Lead-included	100	0°C to 60°C	100	0°C to 60°C	-40°C to 85°C
	V Version							-40°C to 125°C
	T Version	B7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	V Version						-40°C to 125°C	-40°C to 125°C
	T Version	U	Lead-free	100		100	0°C to 60°C	-40°C to 85°C
	V Version							-40°C to 125°C
	T Version	U7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	V Version						-40°C to 125°C	-40°C to 125°C

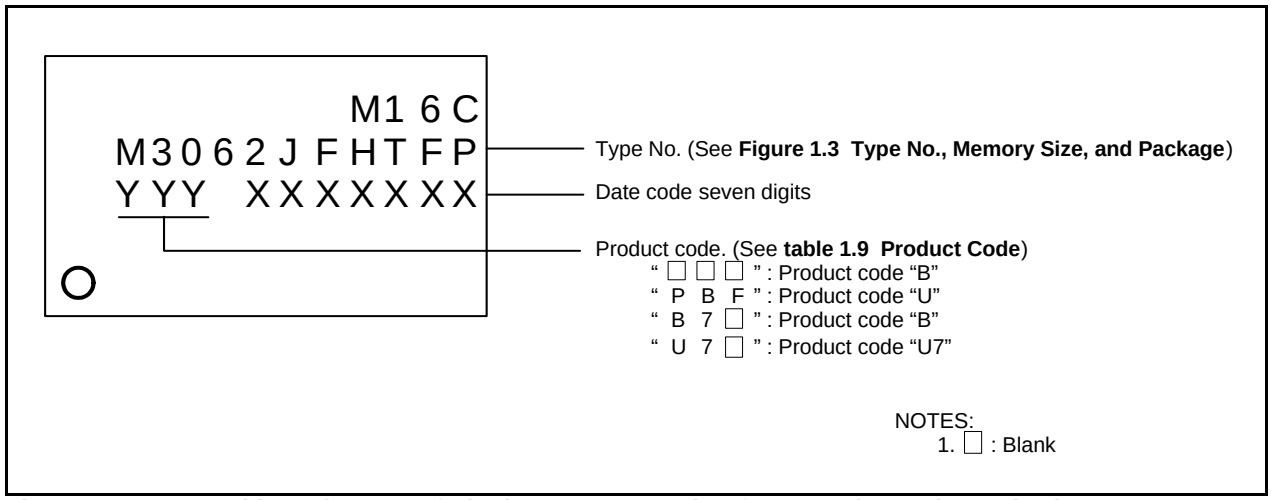


Figure 1.5 Marking Diagram of Flash Memory version for M16C/62PT (Top View)

Table 1.11 Pin Characteristics for 128-Pin Package (2)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
51		P5_6					ALE
52		P5_5					$\overline{\text{HOLD}}$
53		P5_4					$\overline{\text{HLDA}}$
54		P13_3					
55		P13_2					
56		P13_1					
57		P13_0					
58		P5_3					BCLK
59		P5_2					$\overline{\text{RD}}$
60		P5_1					$\overline{\text{WRH}}$/$\overline{\text{BHE}}$
61		P5_0					$\overline{\text{WRL}}$/$\overline{\text{WR}}$
62		P12_7					
63		P12_6					
64		P12_5					
65		P4_7					$\overline{\text{CS3}}$
66		P4_6					$\overline{\text{CS2}}$
67		P4_5					$\overline{\text{CS1}}$
68		P4_4					$\overline{\text{CS0}}$
69		P4_3					A19
70		P4_2					A18
71		P4_1					A17
72		P4_0					A16
73		P3_7					A15
74		P3_6					A14
75		P3_5					A13
76		P3_4					A12
77		P3_3					A11
78		P3_2					A10
79		P3_1					A9
80		P12_4					
81		P12_3					
82		P12_2					
83		P12_1					
84		P12_0					
85	VCC2						
86		P3_0					A8(/-/D7)
87	VSS						
88		P2_7				AN2_7	A7(/D7/D6)
89		P2_6				AN2_6	A6(/D6/D5)
90		P2_5				AN2_5	A5(/D5/D4)
91		P2_4				AN2_4	A4(/D4/D3)
92		P2_3				AN2_3	A3(/D3/D2)
93		P2_2				AN2_2	A2(/D2/D1)
94		P2_1				AN2_1	A1(/D1/D0)
95		P2_0				AN2_0	A0(/D0/-)
96		P1_7	$\overline{\text{INT5}}$				D15
97		P1_6	$\overline{\text{INT4}}$				D14
98		P1_5	$\overline{\text{INT3}}$				D13
99		P1_4					D12
100		P1_3					D11

Table 1.15 Pin Characteristics for 80-Pin Package (1)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
1		P9_5			CLK4	ANEX0	
2		P9_4		TB4IN		DA1	
3		P9_3		TB3IN		DA0	
4		P9_2		TB2IN	SOUT3		
5		P9_0		TB0IN	CLK3		
6	CNVSS (BYTE)						
7	XCIN	P8_7					
8	XCOUT	P8_6					
9	$\overline{\text{RESET}}$						
10	XOUT						
11	VSS						
12	XIN						
13	VCC1						
14		P8_5	$\overline{\text{NMI}}$				
15		P8_4	$\overline{\text{INT2}}$	ZP			
16		P8_3	$\overline{\text{INT1}}$				
17		P8_2	$\overline{\text{INT0}}$				
18		P8_1		TA4IN			
19		P8_0		TA4OUT			
20		P7_7		TA3IN			
21		P7_6		TA3OUT			
22		P7_1		TA0IN/TB5IN	RXD2/SCL2		
23		P7_0		TA0OUT	TXD2/SDA2		
24		P6_7			TXD1/SDA1		
25		P6_6			RXD1/SCL1		
26		P6_5			CLK1		
27		P6_4			$\overline{\text{CTS1}}$/$\overline{\text{RTS1}}$/$\overline{\text{CTS0}}$/CLKS1		
28		P6_3			TXD0/SDA0		
29		P6_2			RXD0/SCL0		
30		P6_1			CLK0		
31		P6_0			$\overline{\text{CTS0}}$/$\overline{\text{RTS0}}$		
32		P5_7					CLKOUT
33		P5_6					
34		P5_5					
35		P5_4					
36		P5_3					
37		P5_2					
38		P5_1					
39		P5_0					
40		P4_3					
41		P4_2					
42		P4_1					
43		P4_0					
44		P3_7					
45		P3_6					
46		P3_5					
47		P3_4					
48		P3_3					
49		P3_2					
50		P3_1					

1.6 Pin Description

Table 1.17 Pin Description (100-pin and 128-pin Version) (1)

Signal Name	Pin Name	I/O Type	Power Supply(3)	Description
Power supply input	VCC1,VCC2 VSS	I	–	Apply 2.7 to 5.5 V to the VCC1 and VCC2 pins and 0 V to the VSS pin. The VCC apply condition is that VCC1 ≥ VCC2. (1, 2)
Analog power supply input	AVCC AVSS	I	VCC1	Applies the power supply for the A/D converter. Connect the AVCC pin to VCC1. Connect the AVSS pin to VSS.
Reset input	$\overline{\text{RESET}}$	I	VCC1	The microcomputer is in a reset state when applying “L” to the this pin.
CNVSS	CNVSS	I	VCC1	Switches processor mode. Connect this pin to VSS to when after a reset to start up in single-chip mode. Connect this pin to VCC1 to start up in microprocessor mode.
External data bus width select input	BYTE	I	VCC1	Switches the data bus in external memory space. The data bus is 16 bits long when the this pin is held "L" and 8 bits long when the this pin is held "H". Set it to either one. Connect this pin to VSS when an single-chip mode.
Bus control pins (4)	D0 to D7	I/O	VCC2	Inputs and outputs data (D0 to D7) when these pins are set as the separate bus.
	D8 to D15	I/O	VCC2	Inputs and outputs data (D8 to D15) when external 16-bit data bus is set as the separate bus.
	A0 to A19	O	VCC2	Output address bits (A0 to A19).
	A0/D0 to A7/D7	I/O	VCC2	Input and output data (D0 to D7) and output address bits (A0 to A7) by timesharing when external 8-bit data bus are set as the multiplexed bus.
	A1/D0 to A8/D7	I/O	VCC2	Input and output data (D0 to D7) and output address bits (A1 to A8) by timesharing when external 16-bit data bus are set as the multiplexed bus.
	$\overline{\text{CS0}}$ to $\overline{\text{CS3}}$	O	VCC2	Output $\overline{\text{CS0}}$ to $\overline{\text{CS3}}$ signals. $\overline{\text{CS0}}$ to $\overline{\text{CS3}}$ are chip-select signals to specify an external space.
	$\overline{\text{WRL}}$/$\overline{\text{WR}}$ $\overline{\text{WRH}}$/$\overline{\text{BHE}}$ $\overline{\text{RD}}$	O	VCC2	Output $\overline{\text{WRL}}$, $\overline{\text{WRH}}$, ($\overline{\text{WR}}$, $\overline{\text{BHE}}$), $\overline{\text{RD}}$ signals. $\overline{\text{WRL}}$ and $\overline{\text{WRH}}$ or $\overline{\text{BHE}}$ and $\overline{\text{WR}}$ can be switched by program. • $\overline{\text{WRL}}$, $\overline{\text{WRH}}$ and $\overline{\text{RD}}$ are selected The $\overline{\text{WRL}}$ signal becomes "L" by writing data to an even address in an external memory space. The $\overline{\text{WRH}}$ signal becomes "L" by writing data to an odd address in an external memory space. The $\overline{\text{RD}}$ pin signal becomes "L" by reading data in an external memory space. • $\overline{\text{WR}}$, $\overline{\text{BHE}}$ and $\overline{\text{RD}}$ are selected The $\overline{\text{WR}}$ signal becomes "L" by writing data in an external memory space. The $\overline{\text{RD}}$ signal becomes "L" by reading data in an external memory space. The $\overline{\text{BHE}}$ signal becomes "L" by accessing an odd address. Select $\overline{\text{WR}}$, $\overline{\text{BHE}}$ and $\overline{\text{RD}}$ for an external 8-bit data bus.
	ALE	O	VCC2	ALE is a signal to latch the address.
	$\overline{\text{HOLD}}$	I	VCC2	While the $\overline{\text{HOLD}}$ pin is held "L", the microcomputer is placed in a hold state.
	$\overline{\text{HLDA}}$	O	VCC2	In a hold state, $\overline{\text{HLDA}}$ outputs a "L" signal.
	$\overline{\text{RDY}}$	I	VCC2	While applying a "L" signal to the $\overline{\text{RDY}}$ pin, the microcomputer is placed in a wait state.

I : Input O : Output I/O : Input and output

Power Supply : Power supplies which relate to the external bus pins are separated as VCC2, thus they can be interfaced using the different voltage as VCC1.

NOTES:

1. In this manual, hereafter, VCC refers to VCC1 unless otherwise noted.
2. In M16C/62PT, apply 4.0 to 5.5 V to the VCC1 and VCC2 pins. Also the apply condition is that VCC1 = VCC2.
3. When use VCC1 > VCC2, contacts due to some points or restrictions to be checked.
4. Bus control pins in M16C/62PT cannot be used.

2.8.8 Stack Pointer Select Flag (U Flag)

ISP is selected when the U flag is “0”; USP is selected when the U flag is “1”.
The U flag is cleared to “0” when a hardware interrupt request is accepted or an INT instruction for software interrupt Nos. 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is configured with three bits, for specification of up to eight processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has priority greater than IPL, the interrupt is enabled.

2.8.10 Reserved Area

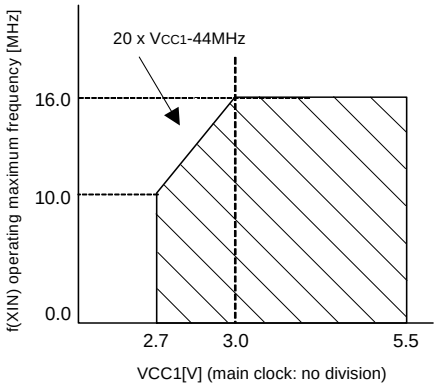
When write to this bit, write “0”. When read, its content is indeterminate.

Table 5.3 Recommended Operating Conditions (2) (1)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
f(XIN)	Main Clock Input Oscillation Frequency (2)	V_{CC1}=3.0V to 5.5V	0		16	MHz
		V_{CC1}=2.7V to 3.0V	0		$20\times V_{CC1}-44$	MHz
f(XCIN)	Sub-Clock Oscillation Frequency			32.768	50	kHz
f(Ring)	On-chip Oscillation Frequency		0.5	1	2	MHz
f(PLL)	PLL Clock Oscillation Frequency (2)	V_{CC1}=3.0V to 5.5V	10		24	MHz
		V_{CC1}=2.7V to 3.0V	10		$46.67\times V_{CC1}-116$	MHz
f(BCLK)	CPU Operation Clock		0		24	MHz
t_{SU}(PLL)	PLL Frequency Synthesizer Stabilization Wait Time	V_{CC1}=5.5V			20	ms
		V_{CC1}=3.0V			50	ms

NOTES:
1. Referenced to V_{CC1} = V_{CC2} = 2.7 to 5.5V at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified.
2. Relationship between main clock oscillation frequency, and supply voltage.

Main clock input oscillation frequency



PLL clock oscillation frequency

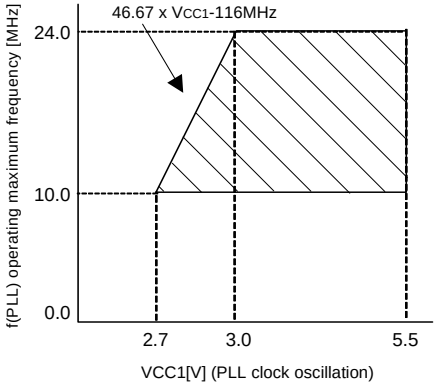


Table 5.6 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (D3, D5, U3, U5)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		10			year

Table 5.7 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (D7, D9, U7, U9) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC1}=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		10			year

NOTES:
1. Referenced to V_{CC1}=4.5 to 5.5V, 3.0 to 3.6V at Topr = 0 to 60 °C (D3, D5, U3, U5) unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Topr = -40 to 85 °C (D3, D7, U3, U7) / -20 to 85 °C (D5, D9, U5, U9).
6. Referenced to V_{CC1} = 4.5 to 5.5V, 3.0 to 3.6V at T_{opr} = -40 to 85 °C (D7, U7) / -20 to 85 °C (D9, U9) unless otherwise specified.
7. Table 5.7 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.6.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (D7, D9, U7 and U9).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.8 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(D3, D5, U3, U5), T_{opr} = -40 to 85 °C(D7, U7) / T_{opr} = -20 to 85 °C(D9, U9))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 3.3 V ± 0.3 V or 5.0 V ± 0.5 V	V_{CC1}=2.7 to 5.5 V

Table 5.9 Low Voltage Detection Circuit Electrical Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det4}	Low Voltage Detection Voltage (1)	V_{CC1}=0.8V to 5.5V	3.3	3.8	4.4	V
V_{det3}	Reset Level Detection Voltage (1, 2)		2.2	2.8	3.6	V
V_{det4}-V_{det3}	Electric potential difference of Low Voltage Detection and Reset Level Detection		0.3			V
V_{det3s}	Low Voltage Reset Retention Voltage				0.8	V
V_{det3r}	Low Voltage Reset Release Voltage (3)		2.2	2.9	4.0	V

NOTES:
1. $V_{det4} > V_{det3}$.
2. Where reset level detection voltage is less than 2.7 V, if the supply power voltage is greater than the reset level detection voltage, the microcomputer operates with f(BCLK) ≤ 10MHz.
3. $V_{det3r} > V_{det3}$ is not guaranteed.
4. The voltage detection circuit is designed to use when VCC1 is set to 5V.

Table 5.10 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for Internal Power Supply Stabilization During Powering-On	V_{CC1}=2.7V to 5.5V			2	ms
$t_{d(R-S)}$	STOP Release Time				150	µs
$t_{d(W-S)}$	Low Power Dissipation Mode Wait Mode Release Time				150	µs
$t_{d(S-R)}$	Brown-out Detection Reset (Hardware Reset 2) Release Wait Time	V_{CC1}=V_{det3r} to 5.5V		6 (1)	20	ms
$t_{d(E-A)}$	Low Voltage Detection Circuit Operation Start Time	V_{CC1}=2.7V to 5.5V			20	µs

NOTES:
1. When V_{CC1} = 5V.

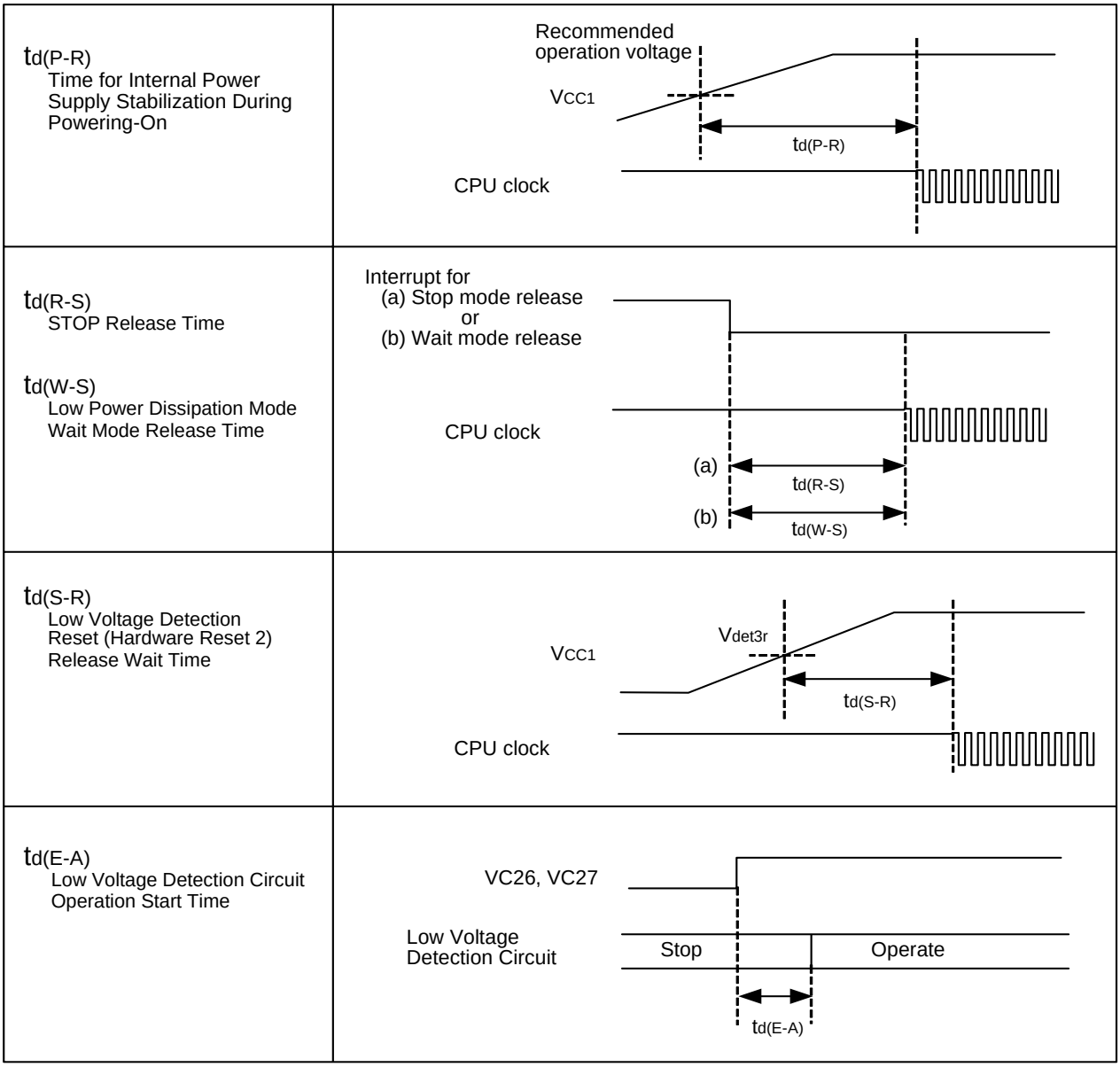


Figure 5.1 Power Supply Circuit Timing Diagram

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.27 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.2**		25	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		4		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			25	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		4		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			15	ns
th(BCLK-ALE)	ALE Signal Output Hold Time		–4		ns
td(BCLK-RD)	RD Signal Output Delay Time			25	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			25	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

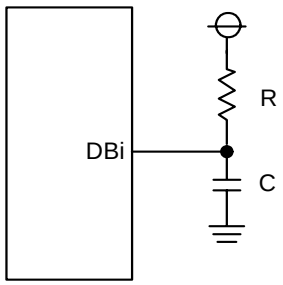
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 40[ns]$$ f(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
   by a circuit of the right figure.
   For example, when $V_{OL} = 0.2V_{CC2}$, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
   = 6.7ns.



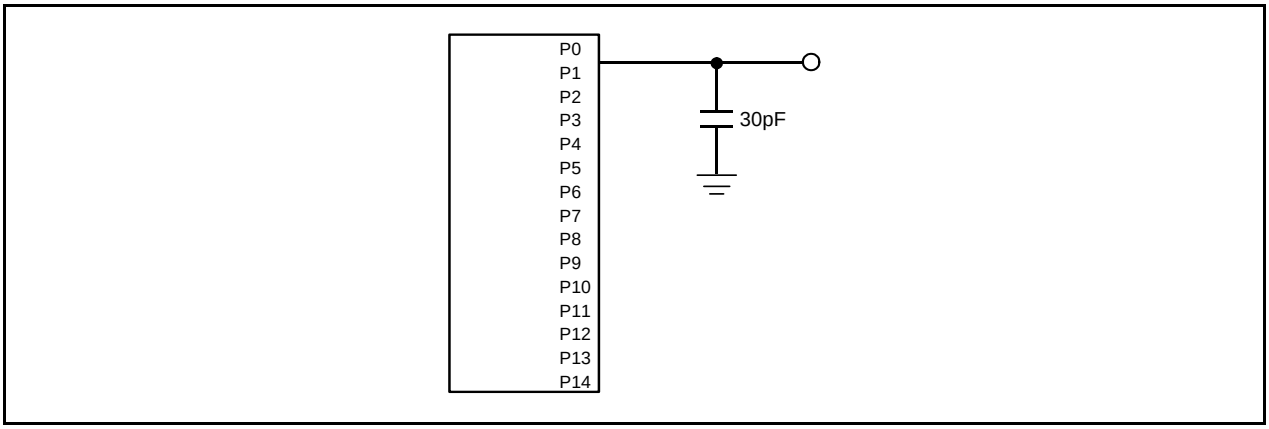


Figure 5.2 Ports P0 to P14 Measurement Circuit

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.28 Memory Expansion and Microprocessor Modes (for 1- to 3-wait setting and external area access)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address Output Delay Time	See **Figure 5.2**		25	ns
$t_{h(BCLK-AD)}$	Address Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-AD)}$	Address Output Hold Time (in relation to RD)		0		ns
$t_{h(WR-AD)}$	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
$t_{d(BCLK-CS)}$	Chip Select Output Delay Time			25	ns
$t_{h(BCLK-CS)}$	Chip Select Output Hold Time (in relation to BCLK)		4		ns
$t_{d(BCLK-ALE)}$	ALE Signal Output Delay Time			15	ns
$t_{h(BCLK-ALE)}$	ALE Signal Output Hold Time		-4		ns
$t_{d(BCLK-RD)}$	RD Signal Output Delay Time			25	ns
$t_{h(BCLK-RD)}$	RD Signal Output Hold Time		0		ns
$t_{d(BCLK-WR)}$	WR Signal Output Delay Time			25	ns
$t_{h(BCLK-WR)}$	WR Signal Output Hold Time		0		ns
$t_{d(BCLK-DB)}$	Data Output Delay Time (in relation to BCLK)			40	ns
$t_{h(BCLK-DB)}$	Data Output Hold Time (in relation to BCLK) (3)		4		ns
$t_{d(DB-WR)}$	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR)(3)		(NOTE 2)		ns
$t_{d(BCLK-HLDA)}$	HLDA Output Delay Time			40	ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

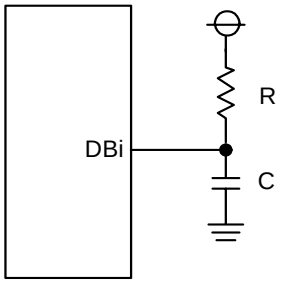
$$\frac{(n-0.5)\times 10^9}{f(BCLK)} - 40[ns]$$

n is “1” for 1-wait setting, “2” for 2-wait setting and “3” for 3-wait setting.
(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times 10^9}{f(BCLK)} - 10[ns]$$

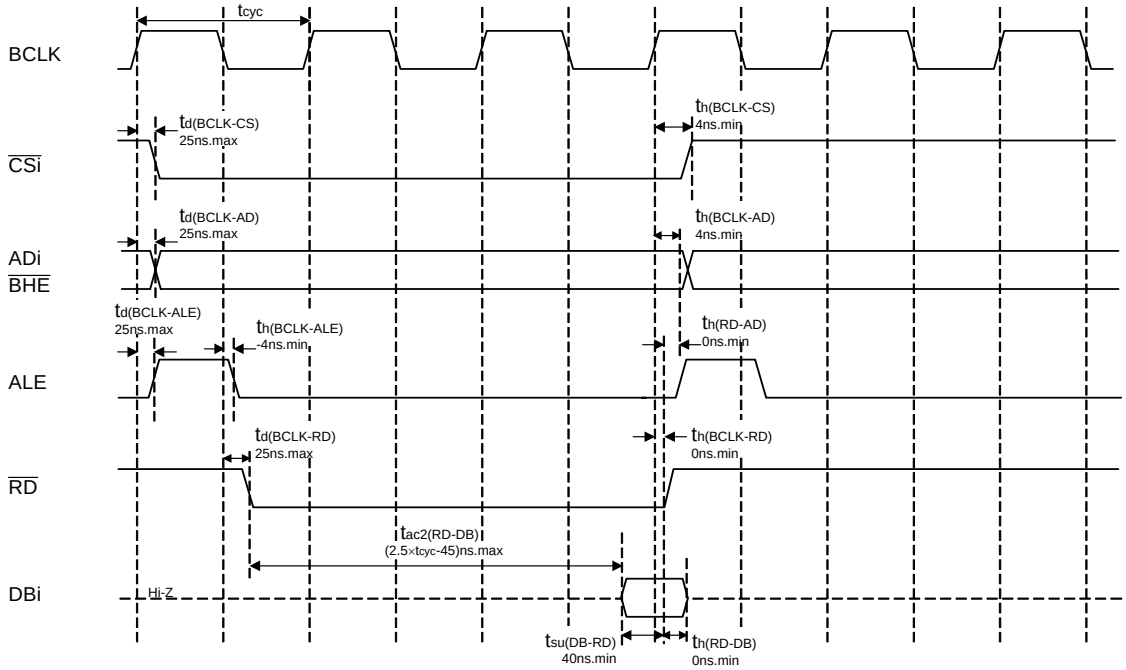
3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
Hold time of data bus is expressed in
$t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
by a circuit of the right figure.
For example, when V_{OL} = 0.2V_{CC2}, C = 30pF, R = 1kΩ, hold time of output ”L” level is
$t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
= 6.7ns.



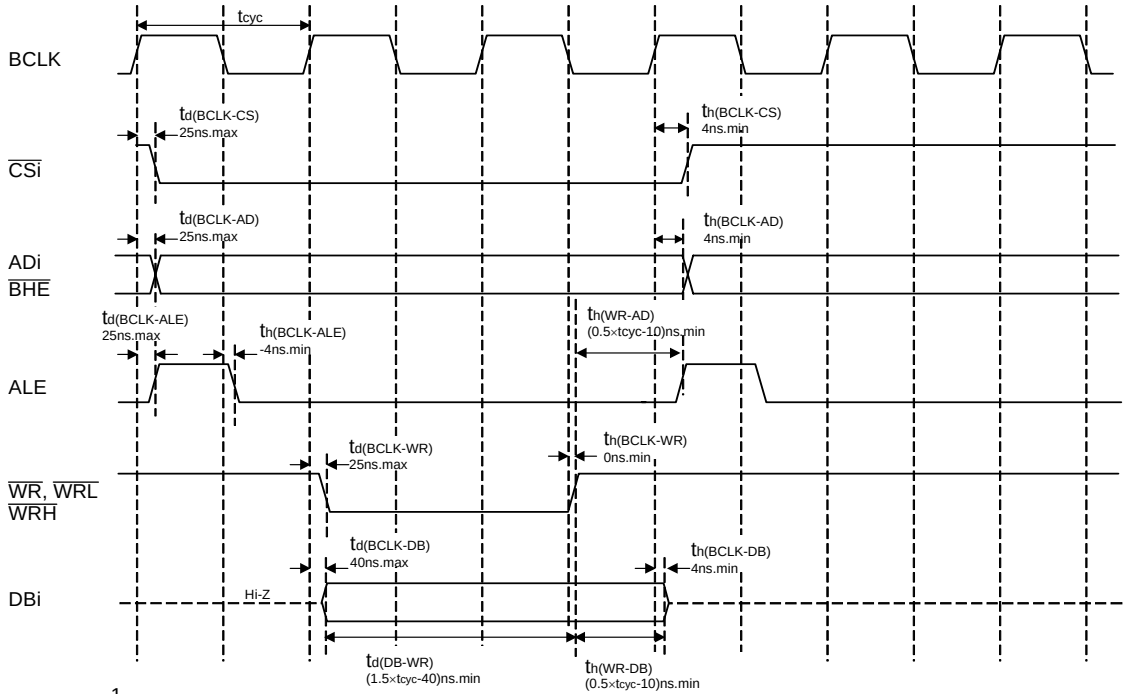
$V_{CC1}=V_{CC2}=5V$

Memory Expansion Mode, Microprocessor Mode
(for 2-wait setting and external area access**)**

Read timing



Write timing



$$T_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
· $V_{CC1}=V_{CC2}=5V$
· Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
· Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

Figure 5.8 Timing Diagram (6)

$V_{CC1}=V_{CC2}=3V$

Timing Requirements
(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.32 External Clock Input (XIN input)(1)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External Clock Input Cycle Time	(NOTE 2)		ns
$t_{w(H)}$	External Clock Input HIGH Pulse Width	(NOTE 3)		ns
$t_{w(L)}$	External Clock Input LOW Pulse Width	(NOTE 3)		ns
t_r	External Clock Rise Time		(NOTE 4)	ns
t_f	External Clock Fall Time		(NOTE 4)	ns

NOTES:
1. The condition is V_{CC1}=V_{CC2}=2.7 to 3.0V.
2. Calculated according to the V_{CC1} voltage as follows:

$$\frac{10^{-6}}{20 \times V_{CC2} - 44} \text{ [ns]}$$

3. Calculated according to the V_{CC1} voltage as follows:

$$\frac{10^{-6}}{20 \times V_{CC1} - 44} \times 0.4 \text{ [ns]}$$

4. Calculated according to the V_{CC1} voltage as follows:

$$-10 \times V_{CC1} + 45 \text{ [ns]}$$

Table 5.33 Memory Expansion Mode and Microprocessor Mode

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{ac1(RD-DB)}$	Data Input Access Time (for setting with no wait)		(NOTE 1)	ns
$t_{ac2(RD-DB)}$	Data Input Access Time (for setting with wait)		(NOTE 2)	ns
$t_{ac3(RD-DB)}$	Data Input Access Time (when accessing multiplex bus area)		(NOTE 3)	ns
$t_{su(DB-RD)}$	Data Input Setup Time	50		ns
$t_{su(RDY-BCLK)}$	$\overline{RDY}$ Input Setup Time	40		ns
$t_{su(HOLD-BCLK)}$	$\overline{HOLD}$ Input Setup Time	50		ns
$t_{h(RD-DB)}$	Data Input Hold Time	0		ns
$t_{h(BCLK-RDY)}$	$\overline{RDY}$ Input Hold Time	0		ns
$t_{h(BCLK-HOLD)}$	$\overline{HOLD}$ Input Hold Time	0		ns

NOTES:
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 60 \text{[ns]}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5) \times 10^9}{f(BCLK)} - 60 \text{[ns]}$$ n is ”2” for 1-wait setting, “3” for 2-wait setting and “4” for 3-wait setting.

3. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5) \times 10^9}{f(BCLK)} - 60 \text{[ns]}$$ n is “2” for 2-wait setting, “3” for 3-wait setting.

$V_{CC1}=V_{CC2}=3V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.46 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.12**		30	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		4		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			30	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		4		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			25	ns
th(BCLK-ALE)	ALE Signal Output Hold Time		–4		ns
td(BCLK-RD)	RD Signal Output Delay Time			30	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			30	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

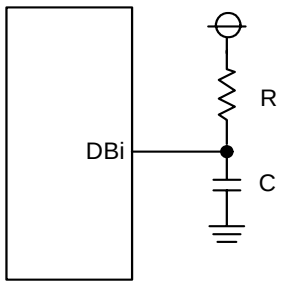
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 40[ns]$$ f(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
   by a circuit of the right figure.
   For example, when $V_{OL} = 0.2V_{CC2}$, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
   = 6.7ns.



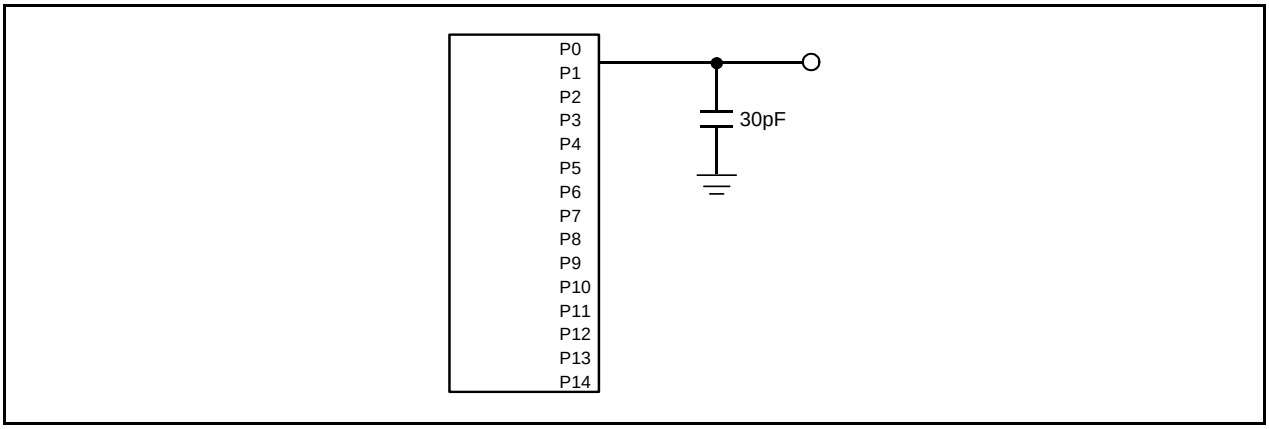


Figure 5.12 Ports P0 to P14 Measurement Circuit

5.2 Electrical Characteristics (M16C/62PT)

Table 5.49 Absolute Maximum Ratings

Symbol	Parameter		Condition	Rated Value	Unit
V_{CC1}, V_{CC2}	Supply Voltage		V_{CC1}=V_{CC2}=AVcc	–0.3 to 6.5	V
AVcc	Analog Supply Voltage		V_{CC1}=V_{CC2}=AVcc	–0.3 to 6.5	V
V_I	Input Voltage	$\overline{\text{RESET}}$, CNVSS, BYTE, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, VREF, XIN		–0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		–0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		–0.3 to 6.5	V
V_O	Output Voltage	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XOUT		–0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		–0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		–0.3 to 6.5	V
P_d	Power Dissipation		–40°C<T_{opr}≤85°C	300	mW
			85°C<T_{opr}≤125°C	200	
T_{opr}	Operating Ambient Temperature	When the Microcomputer is Operating		–40 to 85 / –40 to 125 (2)	°C
		Flash Program Erase		0 to 60	
T_{stg}	Storage Temperature			–65 to 150	°C

NOTES:
1. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.
2. T version = –40 to 85 °C, V version= –40 to 125 °C.

Table 5.51 A/D Conversion Characteristics (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		$V_{REF}=V_{CC1}$				10	Bits
INL	Integral Non-Linearity Error	10bit	$V_{REF}=V_{CC1}=5V$	AN0 to AN7 input, AN0_0 to AN0_7 input, AN2_0 to AN2_7 input, ANEX0, ANEX1 input			±3	LSB
				External operation amp connection mode			±7	LSB
		8bit	$V_{REF}=V_{CC1}=5V$				±2	LSB
–	Absolute Accuracy	10bit	$V_{REF}=V_{CC1}=5V$	AN0 to AN7 input, AN0_0 to AN0_7 input, AN2_0 to AN2_7 input, ANEX0, ANEX1 input			±3	LSB
				External operation amp connection mode			±7	LSB
		8bit	$V_{REF}=V_{CC1}=5V$				±2	LSB
–	Tolerance Level Impedance					3		kΩ
DNL	Differential Non-Linearity Error						±1	LSB
–	Offset Error						±3	LSB
–	Gain Error						±3	LSB
R_{LADDER}	Ladder Resistance		$V_{REF}=V_{CC1}$		10		40	kΩ
t_{CONV}	10-bit Conversion Time, Sample & Hold Function Available		$V_{REF}=V_{CC1}=5V$, ϕAD=12MHz		2.75			µs
t_{CONV}	8-bit Conversion Time, Sample & Hold Function Available		$V_{REF}=V_{CC1}=5V$, ϕAD=12MHz		2.33			µs
t_{SAMP}	Sampling Time				0.25			µs
V_{REF}	Reference Voltage				2.0		V_{CC1}	V
V_{IA}	Analog Input Voltage				0		V_{REF}	V

NOTES:
1. Referenced to $V_{CC1}=AV_{CC}=V_{REF}=4.0$ to 5.5V, $V_{SS}=AV_{SS}=0V$ at T_{opr} = –40 to 85°C / –40 to 125°C unless otherwise specified. T version = –40 to 85°C, V version =–40 to 125°C
2. ϕAD frequency must be 12 MHz or less.
3. When sample & hold is disabled, ϕAD frequency must be 250 kHz or more, in addition to the limitation in Note 2. When sample & hold is enabled, ϕAD frequency must be 1MHz or more, in addition to the limitation in Note 2.

Table 5.52 D/A Conversion Characteristics (1)

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
–	Resolution				8	Bits
–	Absolute Accuracy				1.0	%
t_{SU}	Setup Time				3	µs
R_O	Output Resistance		4	10	20	kΩ
I_{VREF}	Reference Power Supply Input Current	(NOTE 2)			1.5	mA

NOTES:
1. Referenced to $V_{CC1}=V_{REF}=4.0$ to 5.5V, $V_{SS}=AV_{SS}=0V$ at T_{opr} = –40 to 85°C / –40 to 125°C unless otherwise specified. T version = –40 to 85°C, V version =–40 to 125°C
2. This applies when using one D/A converter, with the D/A register for the unused D/A converter set to “00h”. The resistor ladder of the A/D converter is not included. Also, when D/A register contents are not “00h”, the I_{VREF} will flow even if Vref id disconnected by the A/D control register.

Table 5.53 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (B, U)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

Table 5.54 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (B7, U7) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC}1=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

NOTES:
1. Referenced to V_{CC1}=4.5 to 5.5V at T_{opr} = 0 to 60 °C unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Ta (ambient temperature)=55 °C. As to the data hold time except Ta=55 °C, please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor.
6. Referenced to V_{CC1} = 4.5 to 5.5V at T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version)) unless otherwise specified.
7. Table 5.54 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.53.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (B7 and U7).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.55 Flash Memory Version Program/Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(B, U), T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 5.0 V ± 0.5 V	V_{CC1}=4.0 to 5.5 V

Table 5.58 Electrical Characteristics (2) (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
I_{CC}	Power Supply Current (V_{CC1}=V_{CC2}=4.0V to 5.5V)	In single-chip mode, the output pins are open and other pins are V_{SS}	Mask ROM	f(BCLK)=24MHz No division, PLL operation		14	20	mA
				No division, On-chip oscillation		1		mA
			Flash Memory	f(BCLK)=24MHz, No division, PLL operation		18	27	mA
				No division, On-chip oscillation		1.8		mA
			Flash Memory Program	f(BCLK)=10MHz, V_{CC1}=5.0V		15		mA
			Flash Memory Erase	f(BCLK)=10MHz, V_{CC1}=5.0V		25		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM (3)		25		µA
			Flash Memory	f(BCLK)=32kHz Low power dissipation mode, RAM (3)		25		µA
				f(BCLK)=32kHz Low power dissipation mode, Flash Memory (3)		420		µA
				On-chip oscillation, Wait mode		50		µA
			Mask ROM Flash Memory	f(BCLK)=32kHz Wait mode (2), Oscillation capability High		7.5		µA
				f(BCLK)=32kHz Wait mode (2), Oscillation capability Low		2.0		µA
				Stop mode Topr =25°C		2.0	6.0	µA
				Stop mode Topr =85°C			20	µA
				Stop mode Topr =125°C			TBD	µA

NOTES:
1. Referenced to V_{CC1}=V_{CC2}=4.0 to 5.5V, V_{SS} = 0V at T_{opr} = –40 to 85°C / –40 to 125°C, f(BCLK)=24MHz unless otherwise specified. T version = –40 to 85°C, V version =–40 to 125°C.
2. With one timer operated using fC32.
3. This indicates the memory in which the program to be executed exists.

$V_{CC1}=V_{CC2}=5V$

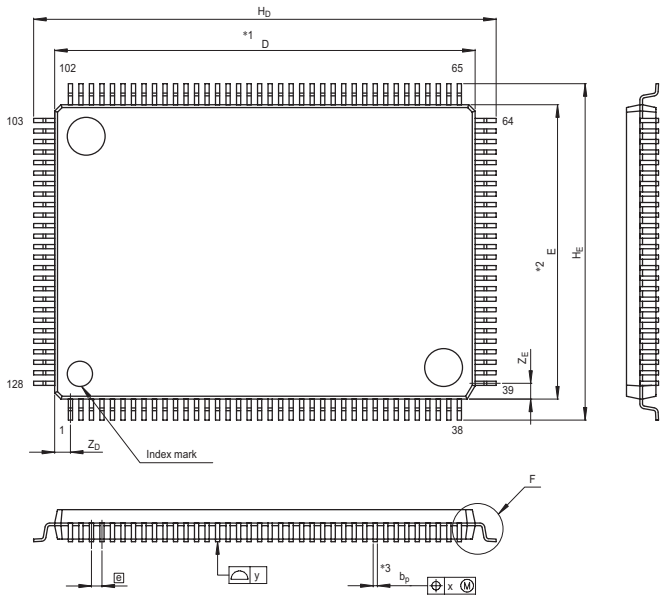
Timing Requirements
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –40 to 85°C (T version) / –40 to 125°C (V version) unless otherwise specified)

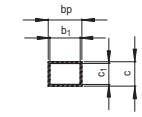
Table 5.59 External Clock Input (XIN input)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External Clock Input Cycle Time	62.5		ns
$t_{w(H)}$	External Clock Input HIGH Pulse Width	25		ns
$t_{w(L)}$	External Clock Input LOW Pulse Width	25		ns
t_r	External Clock Rise Time		15	ns
t_f	External Clock Fall Time		15	ns

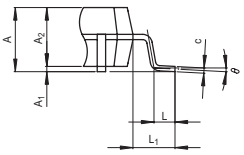
Appendix 1.Package Dimensions

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP128-14x20-0.50	PLQP0128KB-A	128P6Q-A	0.9g





Terminal cross section

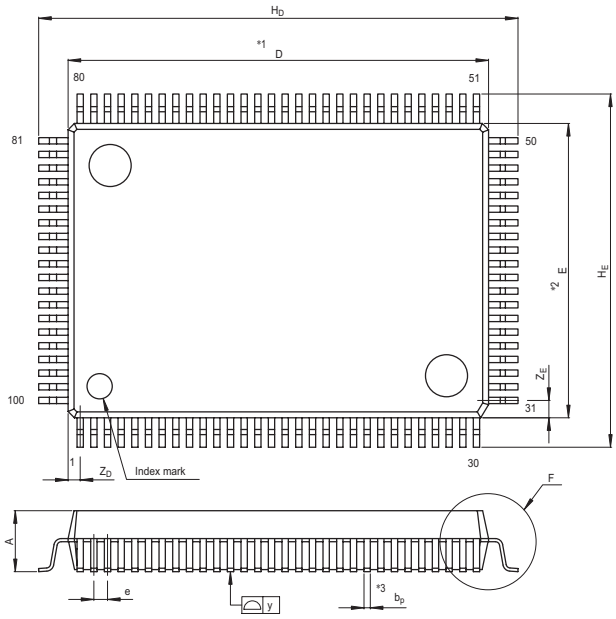


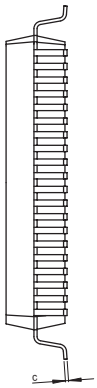
DetailF

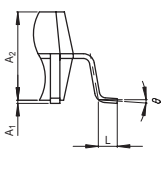
NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	19.9	20.0	20.1
E	13.9	14.0	14.1
A_2	—	1.4	—
H_D	21.8	22.0	22.2
H_E	15.8	16.0	16.2
A	—	—	1.7
A_1	0.05	0.125	0.2
b_p	0.17	0.22	0.27
b_1	—	0.20	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.10
y	—	—	0.10
Z_D	—	0.75	—
Z_E	—	0.75	—
L	0.35	0.5	0.65
L_1	—	1.0	—

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-QFP100-14x20-0.65	PRQP0100JB-A	100P6S-A	1.6g







Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	19.8	20.0	20.2
E	13.8	14.0	14.2
A_2	—	2.8	—
H_D	22.5	22.8	23.1
H_E	16.5	16.8	17.1
A	—	—	3.05
A_1	0	0.1	0.2
b_p	0.25	0.3	0.4
c	0.13	0.15	0.2
θ	0°	—	10°
e	0.5	0.65	0.8
y	—	—	0.10
Z_D	—	0.575	—
Z_E	—	0.825	—
L	0.4	0.6	0.8